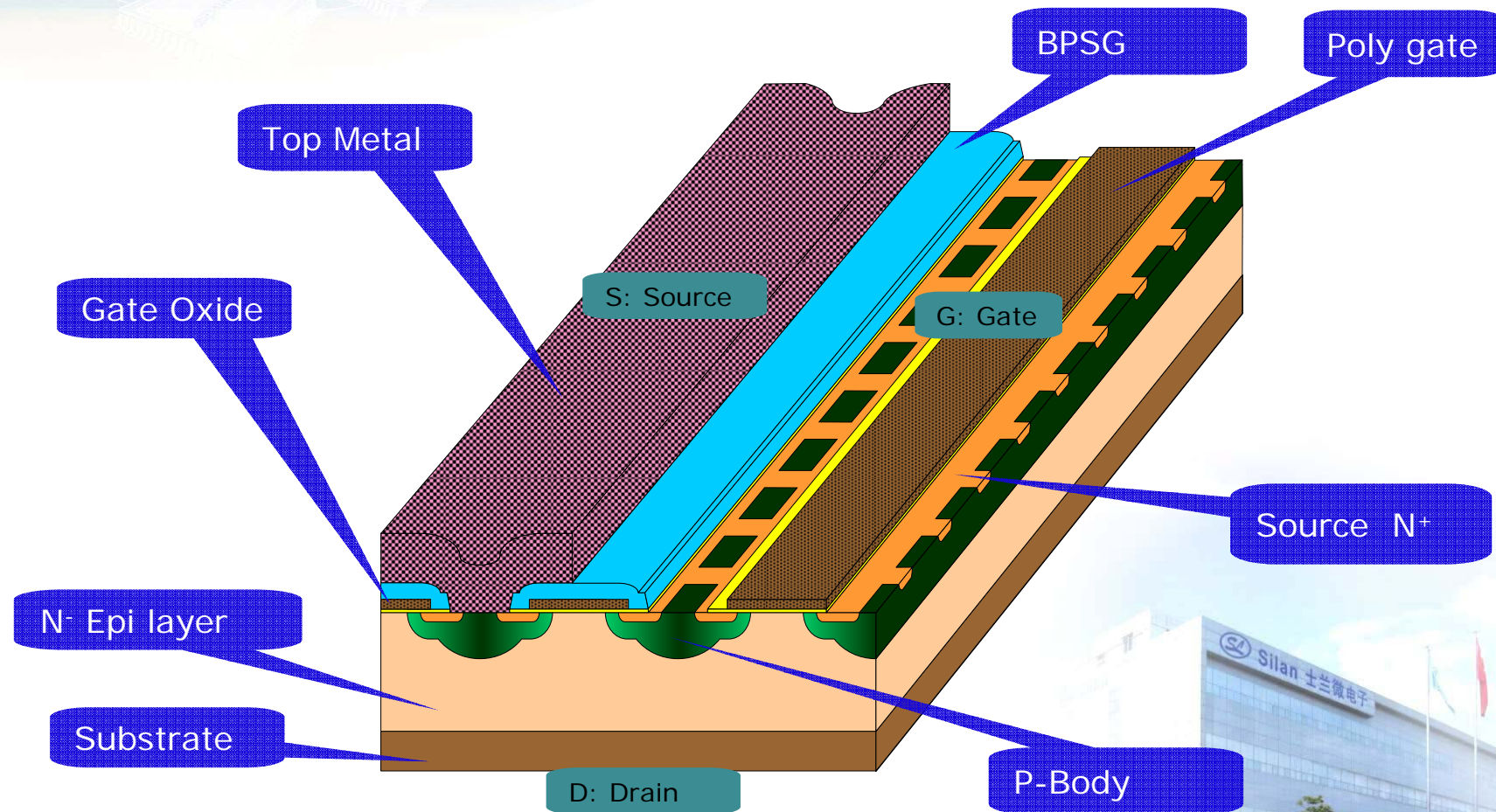


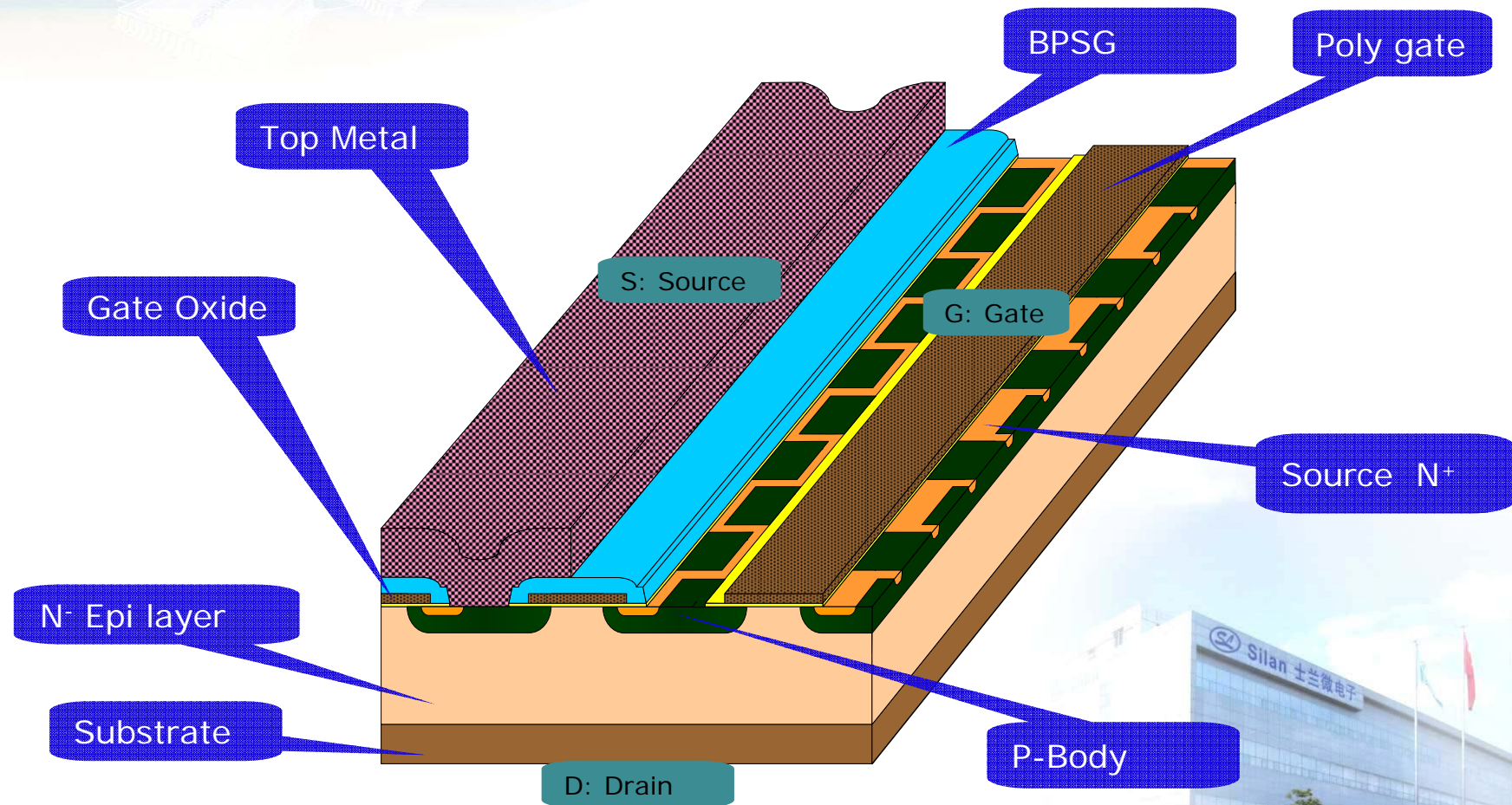


## Cell Structure of SVD830





## Cell Structure of SVF830





## SVF830 Features and Benefits compared with SVD830

- SVF830, which belongs to the new HVDMOS generation named F-Cell, has a smaller chip size compared with SVD830 which belongs to the former generation .
- SVF830 uses the new well-designed guard ring ,which improves the stability of device.
- SVF830 has the faster Switching response Speed due to the smaller capacitances especially the low Crss.
- SVF830 has the better  $R_{dson} \cdot Q_g$  factor.





## SVF830 and SVD830 main parameters comparison

GEN.	Product Name	Spec.	EAS (mJ)	Turn on/off time		Gate charge (VDS=80%Spec.)		
				Turn on time (ns)	Turn off time (ns)	Qgs(nc)	Qgd(nc)	Qg(nc)
S-Rin	SVD830F	5A/500V	256	31	124	2.7	6.1	16
F-Cell	SVF830F	5A/500V	234	52.64	49.2	2.61	3.28	9.04





## SVF830 and SVD830 main parameters comparison

GEN.	Product Name	Spec.	Capacitance			Die Area(Scripe line included) (mm <sup>2</sup> )	Mask Number
			Ciss (pf)	Coss (pf)	Crss (pf)		
S-Rin	SVD830F	5A/500V	548	63	5	3.20x2.88	7
F-Cell	SVF830F	5A/500V	481	71.8	2.14	2.8x2.75	8

